17. The method of claim 16 wherein said photo and electrical energies are supplied sequentially.

18. The method of claim 16 wherein said photo and electrical energies are supplied simultaneously.

19. The method of claim 16 wherein said film comprises silicon oxide.

20. The method of claim 16 wherein said reactive gas further contains an oxidizing gas.

21. The method of claim 20 wherein said oxidizing gas is oxygen.

22. A method of forming a film on a substrate comprising the steps of:

placing a substrate in a reaction chamber;

introducing a reactive gas comprising at least TEOS;

supplying a photo energy to said reactive gas to excite said gas;

depositing a first film on said substrate;

stopping supplying said photo energy;

supplying a photo energy to said reactive gas to excite said gas; and

depositing a second film on said first film.

23. A method of forming a film on a substrate comprising the steps of:

placing a substrate in a reaction chamber;

introducing a reactive gas comprising at least TEOS;

supplying photo energies and plasma energies simultaneously in order to decompose said reactive gas; and

depositing a film on said substrate.

24. The method of claim 22 wherein said first and second films each comprise silicon oxide.

25. The method of claims 16, 22, or 23 where said substrate has a plurality of leads formed thereon.

26. The method of claim 25 wherein said leads comprise aluminum.

27. The method of claim 25 wherein said leads are about 0.8 microns in height, about 0.6 microns in width, and a gap between each lead is about 0.9 microns.

28. The method of claim 25 further comprising the step of forming a buffer layer between said substrate and the film formed on the substrate.

29. The method of claims 16, 22, or 23 wherein said TEOS is in a liquid state during deposition.

30. A method as in claims 16, 22, or 23 where said TEOS is in a gaseous state during deposition.